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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	15
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21324dnsp-w4

1.2 Product List

Table 1.3 lists Product List for R8C/32C Group, and Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/32C Group.

Table 1.3 Product List for R8C/32C Group

Current of Aug 2010

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F21321CNSP	4 Kbytes	1 Kbyte × 4	512 bytes	PLSP0020JB-A	N version
R5F21322CNSP	8 Kbytes	1 Kbyte × 4	1 Kbyte	PLSP0020JB-A	
R5F21324CNSP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLSP0020JB-A	
R5F21321CDSP	4 Kbytes	1 Kbyte × 4	512 bytes	PLSP0020JB-A	D version
R5F21322CDSP	8 Kbytes	1 Kbyte × 4	1 Kbyte	PLSP0020JB-A	
R5F21324CDSP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLSP0020JB-A	

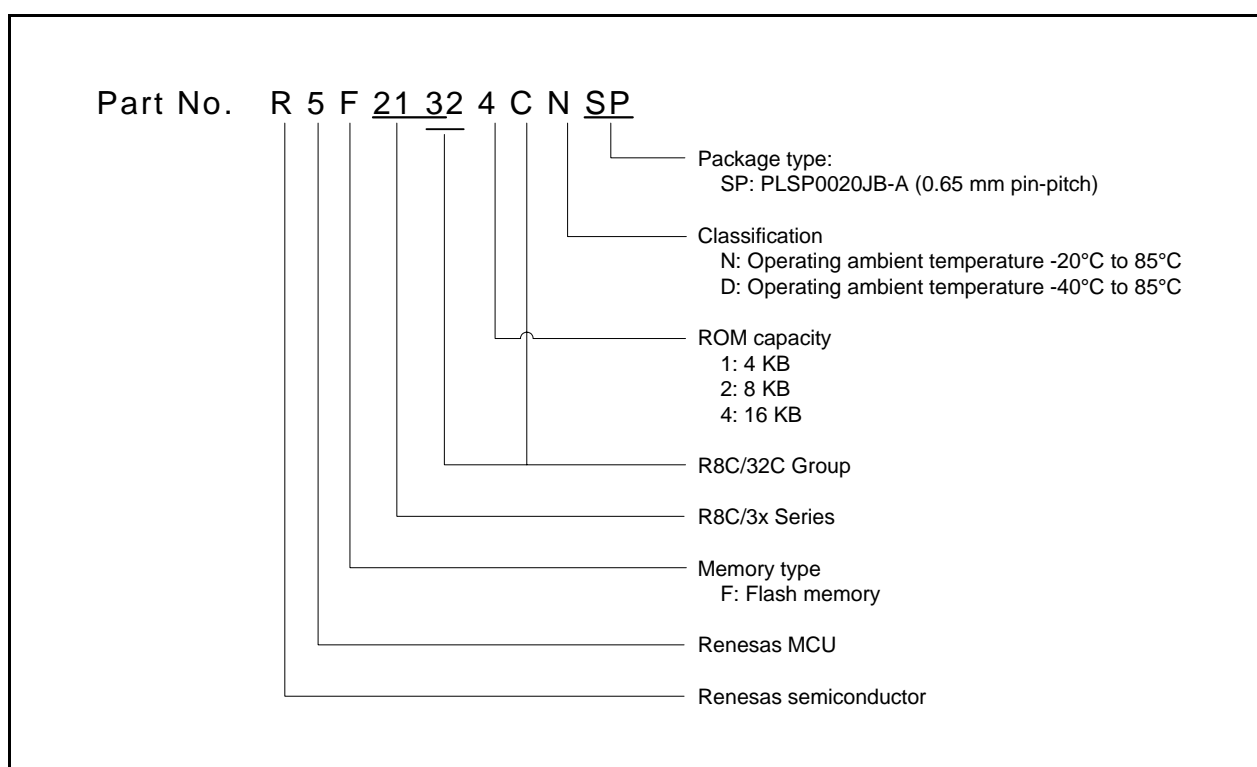


Figure 1.1 Part Number, Memory Size, and Package of R8C/32C Group

1.4 Pin Assignment

Figure 1.3 shows Pin Assignment (Top View). Table 1.4 outlines the Pin Name Information by Pin Number.

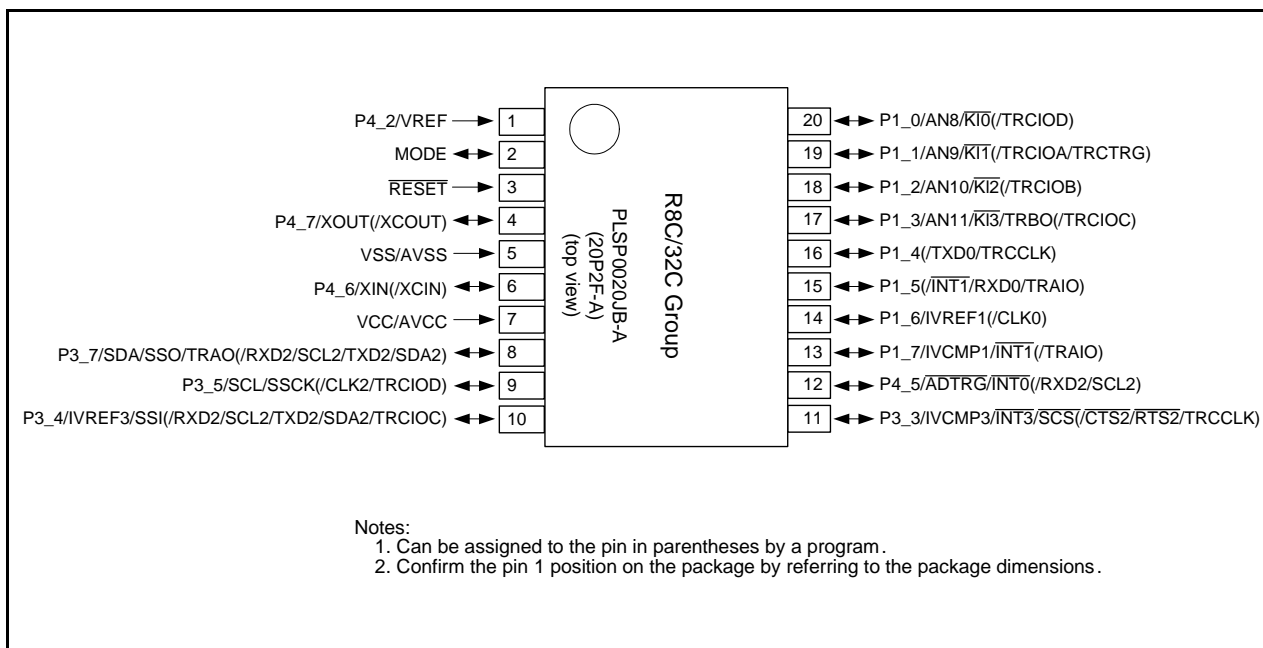


Figure 1.3 Pin Assignment (Top View)

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 and as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the starting address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.

Interrupts are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.

The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide and assigns processor interrupt priority levels from level 0 to level 7.

If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/32C Group

Figure 3.1 is a Memory Map of R8C/32C Group. The R8C/32C Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.

The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1.5-Kbyte internal RAM area is allocated addresses 00400h to 009FFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.

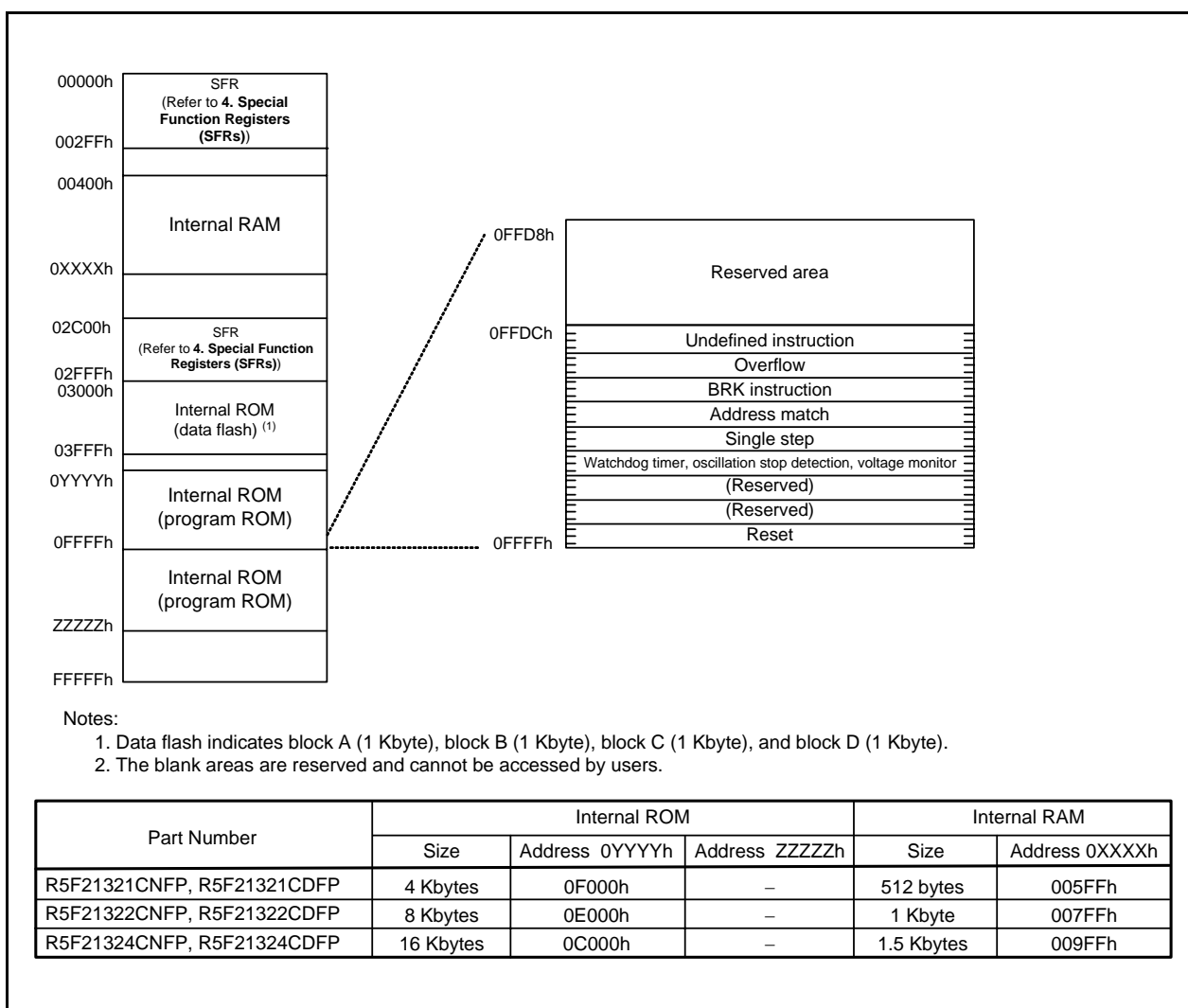


Figure 3.1 Memory Map of R8C/32C Group

Table 4.3 SFR Information (3) (1)

Address	Register	Symbol	After Reset
0080h	DTC Activation Control Register	DTCTL	00h
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h			
0088h	DTC Activation Enable Register 0	DTCEN0	00h
0089h	DTC Activation Enable Register 1	DTCEN1	00h
008Ah	DTC Activation Enable Register 2	DTCEN2	00h
008Bh	DTC Activation Enable Register 3	DTCEN3	00h
008Ch			
008Dh	DTC Activation Enable Register 5	DTCEN5	00h
008Eh	DTC Activation Enable Register 6	DTCEN6	00h
008Fh			
0090h			
0091h			
0092h			
0093h			
0094h			
0095h			
0096h			
0097h			
0098h			
0099h			
009Ah			
009Bh			
009Ch			
009Dh			
009Eh			
009Fh			
00A0h	UART0 Transmit / Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit / Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit / Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART2 Transmit / Receive Mode Register	U2MR	00h
00A9h	UART2 Bit Rate Register	U2BRG	XXh
00AAh	UART2 Transmit Buffer Register	U2TB	XXh
00ABh			XXh
00ACh	UART2 Transmit / Receive Control Register 0	U2C0	00001000b
00ADh	UART2 Transmit / Receive Control Register 1	U2C1	00000010b
00AEh	UART2 Receive Buffer Register	U2RB	XXh
00AFh			XXh
00B0h	UART2 Digital Filter Function Select Register	URXDF	00h
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h			
00B9h			
00BAh			
00BBh	UART2 Special Mode Register 5	U2SMR5	00h
00BCh	UART2 Special Mode Register 4	U2SMR4	00h
00BDh	UART2 Special Mode Register 3	U2SMR3	000X0X0Xb
00BEh	UART2 Special Mode Register 2	U2SMR2	X0000000b
00BFh	UART2 Special Mode Register	U2SMR	X0000000b

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.6 SFR Information (6) (1)

Address	Register	Symbol	After Reset
0140h			
0141h			
0142h			
0143h			
0144h			
0145h			
0146h			
0147h			
0148h			
0149h			
014Ah			
014Bh			
014Ch			
014Dh			
014Eh			
014Fh			
0150h			
0151h			
0152h			
0153h			
0154h			
0155h			
0156h			
0157h			
0158h			
0159h			
015Ah			
015Bh			
015Ch			
015Dh			
015Eh			
015Fh			
0160h			
0161h			
0162h			
0163h			
0164h			
0165h			
0166h			
0167h			
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h			
0171h			
0172h			
0173h			
0174h			
0175h			
0176h			
0177h			
0178h			
0179h			
017Ah			
017Bh			
017Ch			
017Dh			
017Eh			
017Fh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.8 SFR Information (8) (1)

Address	Register	Symbol	After Reset
01C0h	Address Match Interrupt Register 0	RMAD0	XXh
01C1h			XXh
01C2h			0000XXXXb
01C3h	Address Match Interrupt Enable Register 0	AIER0	00h
01C4h	Address Match Interrupt Register 1	RMAD1	XXh
01C5h			XXh
01C6h			0000XXXXb
01C7h	Address Match Interrupt Enable Register 1	AIER1	00h
01C8h			
01C9h			
01CAh			
01CBh			
01CCh			
01CDh			
01CEh			
01CFh			
01D0h			
01D1h			
01D2h			
01D3h			
01D4h			
01D5h			
01D6h			
01D7h			
01D8h			
01D9h			
01DAh			
01DBh			
01DCh			
01DDh			
01DEh			
01DFh			
01E0h	Pull-Up Control Register 0	PUR0	00h
01E1h	Pull-Up Control Register 1	PUR1	00h
01E2h			
01E3h			
01E4h			
01E5h			
01E6h			
01E7h			
01E8h			
01E9h			
01EAh			
01EBh			
01ECh			
01EDh			
01EEh			
01EFh			
01F0h	Port P1 Drive Capacity Control Register	P1DRC	00h
01F1h			
01F2h	Drive Capacity Control Register 0	DRR0	00h
01F3h	Drive Capacity Control Register 1	DRR1	00h
01F4h			
01F5h	Input Threshold Control Register 0	VLT0	00h
01F6h	Input Threshold Control Register 1	VLT1	00h
01F7h			
01F8h	Comparator B Control Register 0	INTCMP	00h
01F9h			
01FAh	External Input Enable Register 0	INTEN	00h
01FBh			
01FCh	INT Input Filter Select Register 0	INTF	00h
01FDh			
01FEh	Key Input Enable Register 0	KIEN	00h
01FFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.11 SFR Information (11) (1)

Address	Register	Symbol	After Reset
2CB0h	DTC Control Data 14	DTCD14	XXh
2CB1h			XXh
2CB2h			XXh
2CB3h			XXh
2CB4h			XXh
2CB5h			XXh
2CB6h			XXh
2CB7h			XXh
2CB8h	DTC Control Data 15	DTCD15	XXh
2CB9h			XXh
2CBAh			XXh
2CBBh			XXh
2CBCh			XXh
2CBDh			XXh
2CBEh			XXh
2CBFh			XXh
2CC0h	DTC Control Data 16	DTCD16	XXh
2CC1h			XXh
2CC2h			XXh
2CC3h			XXh
2CC4h			XXh
2CC5h			XXh
2CC6h			XXh
2CC7h			XXh
2CC8h	DTC Control Data 17	DTCD17	XXh
2CC9h			XXh
2CCAh			XXh
2CCBh			XXh
2CCCh			XXh
2CCDh			XXh
2CCEh			XXh
2CCFh			XXh
2CD0h	DTC Control Data 18	DTCD18	XXh
2CD1h			XXh
2CD2h			XXh
2CD3h			XXh
2CD4h			XXh
2CD5h			XXh
2CD6h			XXh
2CD7h			XXh
2CD8h	DTC Control Data 19	DTCD19	XXh
2CD9h			XXh
2CDAh			XXh
2CDBh			XXh
2CDCh			XXh
2CDDh			XXh
2CDEh			XXh
2CDFh			XXh
2CE0h	DTC Control Data 20	DTCD20	XXh
2CE1h			XXh
2CE2h			XXh
2CE3h			XXh
2CE4h			XXh
2CE5h			XXh
2CE6h			XXh
2CE7h			XXh
2CE8h	DTC Control Data 21	DTCD21	XXh
2CE9h			XXh
2CEAh			XXh
2CEBh			XXh
2CECh			XXh
2CEDh			XXh
2CEEh			XXh
2CEFh			XXh

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.12 SFR Information (12) ⁽¹⁾

Address	Register	Symbol	After Reset
2CF0h	DTC Control Data 22	DTCD22	XXh
2CF1h			XXh
2CF2h			XXh
2CF3h			XXh
2CF4h			XXh
2CF5h			XXh
2CF6h			XXh
2CF7h			XXh
2CF8h	DTC Control Data 23	DTCD23	XXh
2CF9h			XXh
2CFAh			XXh
2CFBh			XXh
2CFCh			XXh
2CFDh			XXh
2CFEh			XXh
2CFFh			XXh
2D00h			
⋮			
2FFFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.13 ID Code Areas and Option Function Select Area

Address	Area Name	Symbol	After Reset
⋮			
FFDBh	Option Function Select Register 2	OFS2	(Note 1)
⋮			
FFDFh	ID1		(Note 2)
⋮			
FFE3h	ID2		(Note 2)
⋮			
FFEBh	ID3		(Note 2)
⋮			
FFEFh	ID4		(Note 2)
⋮			
FFF3h	ID5		(Note 2)
⋮			
FFF7h	ID6		(Note 2)
⋮			
FFFBh	ID7		(Note 2)
⋮			
FFFFh	Option Function Select Register	OFS	(Note 1)

Notes:

1. The option function select area is allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program. Do not write additions to the option function select area. If the block including the option function select area is erased, the option function select area is set to FFh. When blank products are shipped, the option function select area is set to FFh. It is set to the written value after written by the user. When factory-programming products are shipped, the value of the option function select area is the value programmed by the user.
2. The ID code areas are allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program. Do not write additions to the ID code areas. If the block including the ID code areas is erased, the ID code areas are set to FFh. When blank products are shipped, the ID code areas are set to FFh. They are set to the written value after written by the user. When factory-programming products are shipped, the value of the ID code areas is the value programmed by the user.

Table 5.2 Recommended Operating Conditions

Symbol	Parameter				Conditions	Standard			Unit	
						Min.	Typ.	Max.		
Vcc/AVcc	Supply voltage					1.8	–	5.5	V	
Vss/AVss	Supply voltage					–	0	–	V	
VIH	Input “H” voltage	Other than CMOS input					0.8 Vcc	–	Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection : 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.5 Vcc	–	Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0.55 Vcc	–	Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0.65 Vcc	–	Vcc	V	
			Input level selection : 0.5 Vcc		4.0 V ≤ Vcc ≤ 5.5 V	0.65 Vcc	–	Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0.7 Vcc	–	Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0.8 Vcc	–	Vcc	V	
			Input level selection : 0.7 Vcc		4.0 V ≤ Vcc ≤ 5.5 V	0.85 Vcc	–	Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0.85 Vcc	–	Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0.85 Vcc	–	Vcc	V	
		External clock input (XOUT)					1.2	–	Vcc	V
	VIL	Input “L” voltage	Other than CMOS input					0	–	0.2 Vcc
CMOS input			Input level switching function (I/O port)	Input level selection : 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.2 Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0	–	0.2 Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0	–	0.2 Vcc	V	
			Input level selection : 0.5 Vcc		4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.4 Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0	–	0.3 Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0	–	0.2 Vcc	V	
			Input level selection : 0.7 Vcc		4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.55 Vcc	V	
					2.7 V ≤ Vcc < 4.0 V	0	–	0.45 Vcc	V	
					1.8 V ≤ Vcc < 2.7 V	0	–	0.35 Vcc	V	
External clock input (XOUT)					0	–	0.4	V		
IOH(sum)		Peak sum output “H” current	Sum of all pins IOH(peak)		–	–	–160	mA		
IOH(sum)	Average sum output “H” current	Sum of all pins IOH(avg)		–	–	–80	mA			
IOH(peak)	Peak output “H” current	Drive capacity Low		–	–	–10	mA			
		Drive capacity High		–	–	–40	mA			
IOH(avg)	Average output “H” current	Drive capacity Low		–	–	–5	mA			
		Drive capacity High		–	–	–20	mA			
IOL(sum)	Peak sum output “L” current	Sum of all pins IOL(peak)		–	–	160	mA			
IOL(sum)	Average sum output “L” current	Sum of all pins IOL(avg)		–	–	80	mA			
IOL(peak)	Peak output “L” current	Drive capacity Low		–	–	10	mA			
		Drive capacity High		–	–	40	mA			
IOL(avg)	Average output “L” current	Drive capacity Low		–	–	5	mA			
		Drive capacity High		–	–	20	mA			
f(XIN)	XIN clock input oscillation frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz	
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz	
f(XCIN)	XCIN clock input oscillation frequency				1.8 V ≤ Vcc ≤ 5.5 V	–	32.768	50	kHz	
fOCO40M	When used as the count source for timer RC (3)				2.7 V ≤ Vcc ≤ 5.5 V	32	–	40	MHz	
fOCO-F	fOCO-F frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz	
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz	
–	System clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz	
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz	
f(BCLK)	CPU clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz	
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz	

Notes:

1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. f_{OCO40M} can be used as the count source for timer RC in the range of V_{CC} = 2.7 V to 5.5V.

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
—	Resolution		Vref = AVcc		—	—	10	Bit
—	Absolute accuracy	10-bit mode	Vref = AVcc = 5.0 V	AN8 to AN11 input	—	—	±3	LSB
			Vref = AVcc = 3.3 V	AN8 to AN11 input	—	—	±5	LSB
			Vref = AVcc = 3.0 V	AN8 to AN11 input	—	—	±5	LSB
			Vref = AVcc = 2.2 V	AN8 to AN11 input	—	—	±5	LSB
		8-bit mode	Vref = AVcc = 5.0 V	AN8 to AN11 input	—	—	±2	LSB
			Vref = AVcc = 3.3 V	AN8 to AN11 input	—	—	±2	LSB
			Vref = AVcc = 3.0 V	AN8 to AN11 input	—	—	±2	LSB
			Vref = AVcc = 2.2 V	AN8 to AN11 input	—	—	±2	LSB
φAD	A/D conversion clock		4.0 V ≤ Vref = AVcc ≤ 5.5 V (2)		2	—	20	MHz
			3.2 V ≤ Vref = AVcc ≤ 5.5 V (2)		2	—	16	MHz
			2.7 V ≤ Vref = AVcc ≤ 5.5 V (2)		2	—	10	MHz
			2.2 V ≤ Vref = AVcc ≤ 5.5 V (2)		2	—	5	MHz
—	Tolerance level impedance				—	3	—	kΩ
tCONV	Conversion time	10-bit mode	Vref = AVcc = 5.0 V, φAD = 20 MHz		2.2	—	—	μs
		8-bit mode	Vref = AVcc = 5.0 V, φAD = 20 MHz		2.2	—	—	μs
tsAMP	Sampling time		φAD = 20 MHz		0.8	—	—	μs
IVref	Vref current		Vcc = 5 V, XIN = f1 = φAD = 20 MHz		—	45	—	μA
Vref	Reference voltage				2.2	—	AVcc	V
VIA	Analog input voltage (3)				0	—	Vref	V
OCVREF	On-chip reference voltage		2 MHz ≤ φAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:

- $V_{CC}/AV_{CC} = V_{ref} = 2.2\text{ to }5.5\text{ V}$, $V_{SS} = 0\text{ V}$ and $T_{opr} = -20\text{ to }85^\circ\text{C}$ (N version) / $-40\text{ to }85^\circ\text{C}$ (D version), unless otherwise specified.
- The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
- When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.4 Comparator B Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
Vref	IVREF1, IVREF3 input reference voltage		0	—	$V_{CC} - 1.4$	V
VI	IVCMP1, IVCMP3 input voltage		-0.3	—	$V_{CC} + 0.3$	V
—	Offset		—	5	100	mV
td	Comparator output delay time ⁽²⁾	$V_I = V_{ref} \pm 100\text{ mV}$	—	0.1	—	μs
ICMP	Comparator operating current	$V_{CC} = 5.0\text{ V}$	—	17.5	—	μA

Notes:

- $V_{CC} = 2.7\text{ to }5.5\text{ V}$, $T_{opr} = -20\text{ to }85^\circ\text{C}$ (N version) / $-40\text{ to }85^\circ\text{C}$ (D version), unless otherwise specified.
- When the digital filter is disabled.

Table 5.5 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾		1,000 ⁽³⁾	—	—	times
—	Byte program time		—	80	500	μs
—	Block erase time		—	0.3	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	μs
—	Time from suspend until erase restart		—	—	30+CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		—	—	30+CPU clock × 1 cycle	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time ⁽⁷⁾	Ambient temperature = 55°C	20	—	—	year

Notes:

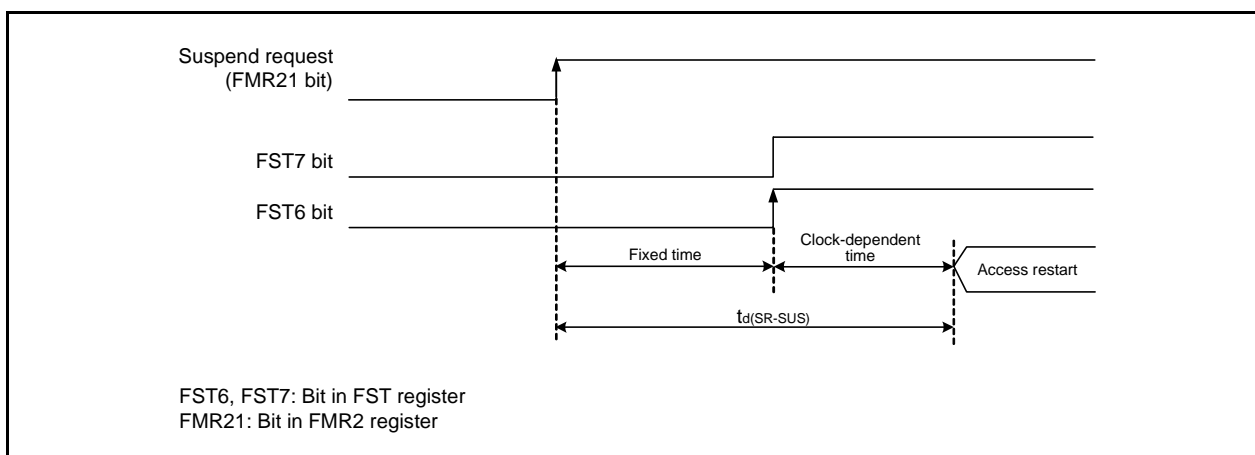
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.6 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance ⁽²⁾		10,000 ⁽³⁾	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	160	1,500	μs
–	Byte program time (program/erase endurance > 1,000 times)		–	300	1,500	μs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	1	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	1	s
t _d (SR-SUS)	Time delay from suspend request until suspend		–	–	5 + CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	μs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	μs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 ⁽⁷⁾	–	85	°C
–	Data hold time ⁽⁸⁾	Ambient temperature = 55 °C	20	–	–	year

Notes:

1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40°C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

**Figure 5.2 Time delay until Suspend**

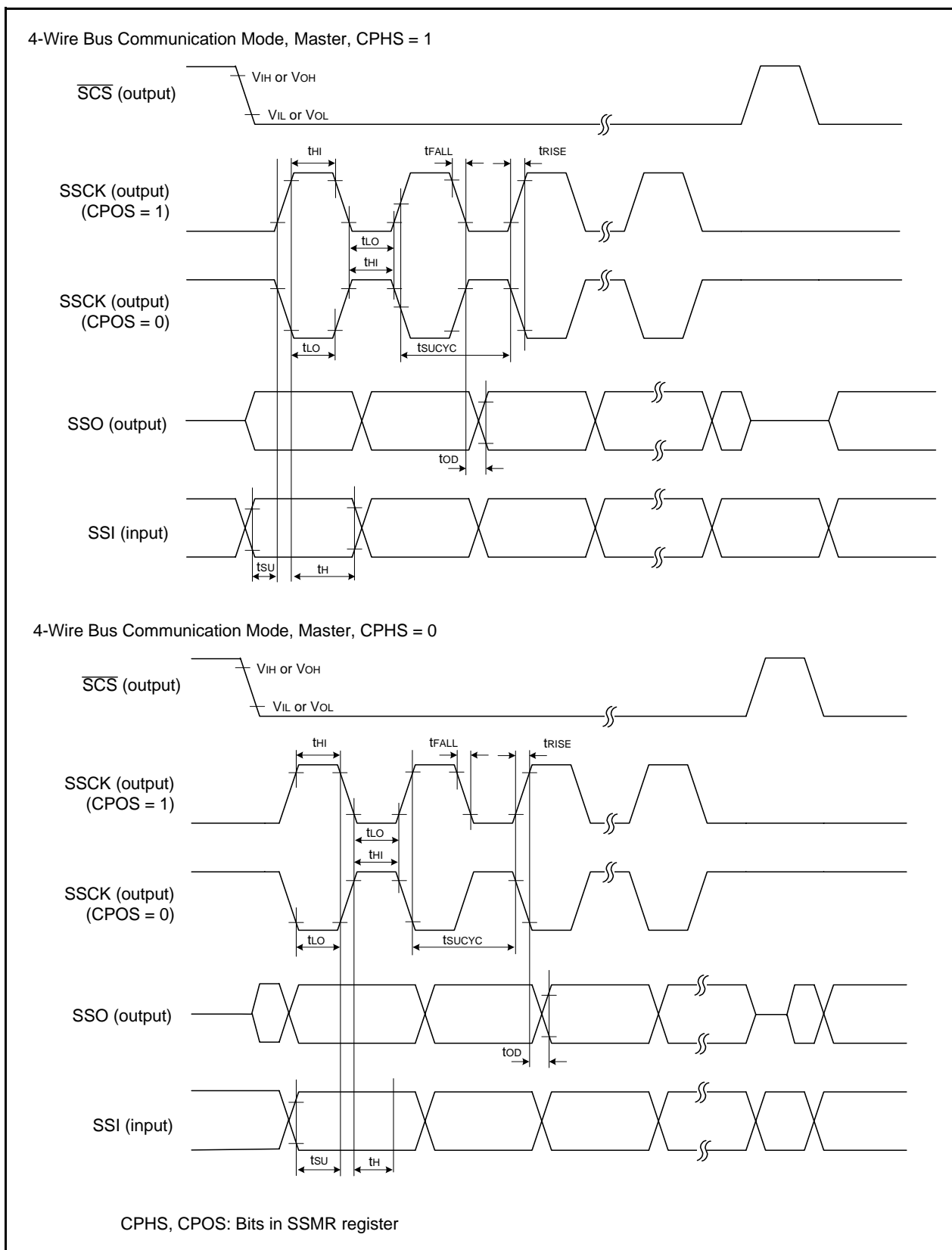


Figure 5.4 I/O Timing of Synchronous Serial Communication Unit (SSU) (Master)

Table 5.16 Electrical Characteristics (1) [4.2 V ≤ V_{CC} ≤ 5.5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output “H” voltage	Other than XOUT	Drive capacity High V _{CC} = 5 V	I _{OH} = −20 mA	V _{CC} − 2.0	−	V _{CC}	V
			Drive capacity Low V _{CC} = 5 V	I _{OH} = −5 mA	V _{CC} − 2.0	−	V _{CC}	V
		XOUT	V _{CC} = 5 V	I _{OH} = −200 μA	1.0	−	V _{CC}	V
V _{OL}	Output “L” voltage	Other than XOUT	Drive capacity High V _{CC} = 5 V	I _{OL} = 20 mA	−	−	2.0	V
			Drive capacity Low V _{CC} = 5 V	I _{OL} = 5 mA	−	−	2.0	V
		XOUT	V _{CC} = 5 V	I _{OL} = 200 μA	−	−	0.5	V
V _{T+} -V _{T-}	Hysteresis	$\overline{\text{INT0}}, \overline{\text{INT1}}, \overline{\text{INT3}},$ $\overline{\text{KI0}}, \overline{\text{KI1}}, \overline{\text{KI2}}, \overline{\text{KI3}},$ $\overline{\text{TRAIO}}, \overline{\text{TRBO}},$ $\overline{\text{TRCIOA}}, \overline{\text{TRCIOB}},$ $\overline{\text{TRCIOC}}, \overline{\text{TRCIOD}},$ $\overline{\text{TRCTRG}},$ $\overline{\text{TRCCLK}}, \overline{\text{ADTRG}},$ $\overline{\text{RXD0}}, \overline{\text{RXD2}},$ $\overline{\text{CLK0}}, \overline{\text{CLK2}},$ $\overline{\text{SSI}}, \overline{\text{SCL}}, \overline{\text{SDA}},$ $\overline{\text{SSO}}$			0.1	1.2	−	V
		$\overline{\text{RESET}}$			0.1	1.2	−	V
I _{IH}	Input “H” current		V _I = 5 V, V _{CC} = 5.0 V		−	−	5.0	μA
I _{IL}	Input “L” current		V _I = 0 V, V _{CC} = 5.0 V		−	−	−5.0	μA
R _{PULLUP}	Pull-up resistance		V _I = 0 V, V _{CC} = 5.0 V		25	50	100	kΩ
R _{FXIN}	Feedback resistance	XIN			−	0.3	−	MΩ
R _{FXCIN}	Feedback resistance	XCIN			−	8	−	MΩ
V _{RAM}	RAM hold voltage		During stop mode		1.8	−	−	V

Note:

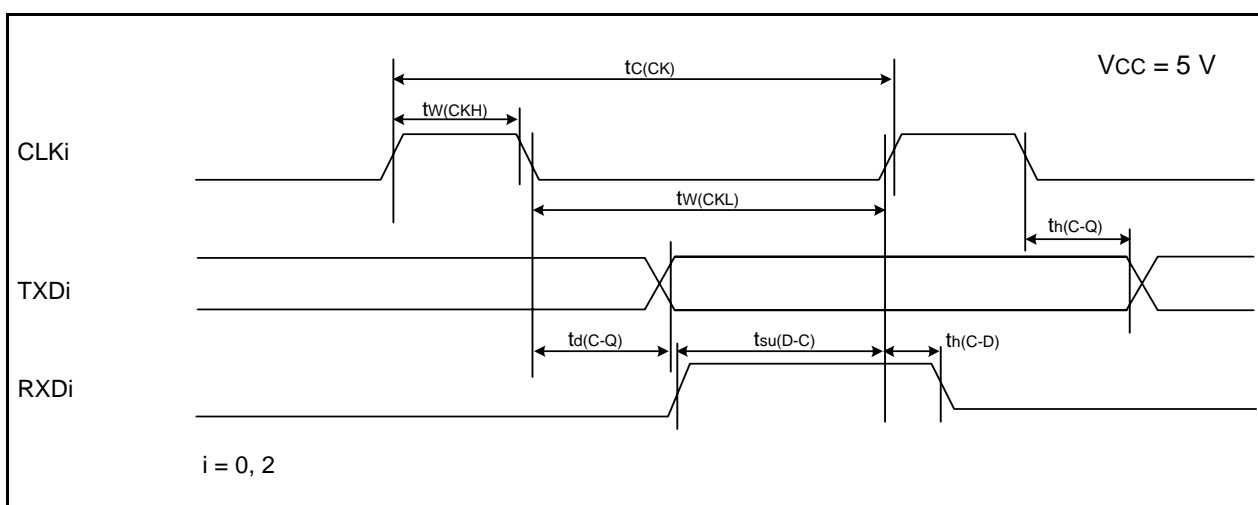
1. 4.2 V ≤ V_{CC} ≤ 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.17 Electrical Characteristics (2) [$3.3\text{ V} \leq V_{CC} \leq 5.5\text{ V}$]
($T_{opr} = -20\text{ to }85^{\circ}\text{C}$ (N version) / $-40\text{ to }85^{\circ}\text{C}$ (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	3.6	—	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	2.2	—	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	—	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	400	μA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	—	85	400	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	—	47	—	μA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	—	15	100	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	—	4	90	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	—	3.5	—	μA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5.0	μA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	5.0	—	μA

Table 5.20 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	—	ns
$t_{w(CKH)}$	CLKi input "H" width	100	—	ns
$t_{w(CKL)}$	CLKi input "L" width	100	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	50	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

 $i = 0, 2$ **Figure 5.10 Serial Interface Timing Diagram when $V_{CC} = 5\text{ V}$** **Table 5.21 External Interrupt \overline{INTi} ($i = 0, 1, 3$) Input, Key Input Interrupt \overline{Kli} ($i = 0$ to 3)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	\overline{INTi} input "H" width, \overline{Kli} input "H" width	250 ⁽¹⁾	—	ns
$t_{w(INL)}$	\overline{INTi} input "L" width, \overline{Kli} input "L" width	250 ⁽²⁾	—	ns

Notes:

- When selecting the digital filter by the \overline{INTi} input filter select bit, use an \overline{INTi} input HIGH width of either (1/digital filter clock frequency \times 3) or the minimum value of standard, whichever is greater.
- When selecting the digital filter by the \overline{INTi} input filter select bit, use an \overline{INTi} input LOW width of either (1/digital filter clock frequency \times 3) or the minimum value of standard, whichever is greater.

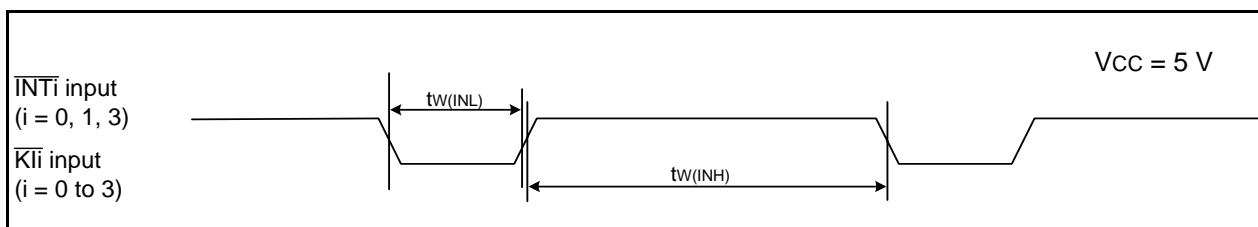
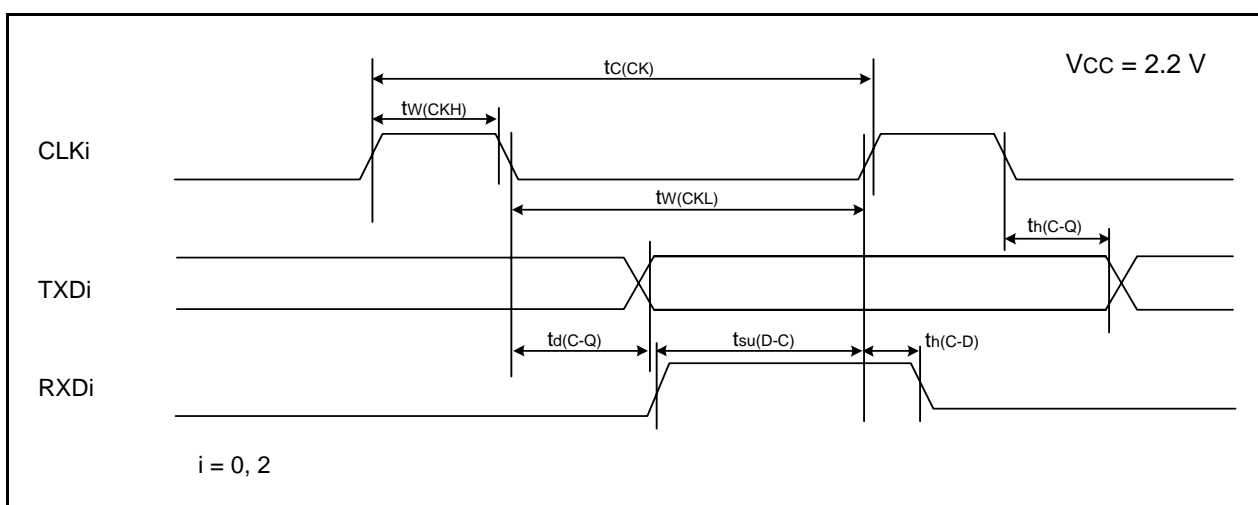
**Figure 5.11 Input Timing Diagram for External Interrupt \overline{INTi} and Key Input Interrupt \overline{Kli} when $V_{CC} = 5\text{ V}$**

Table 5.32 Serial Interface

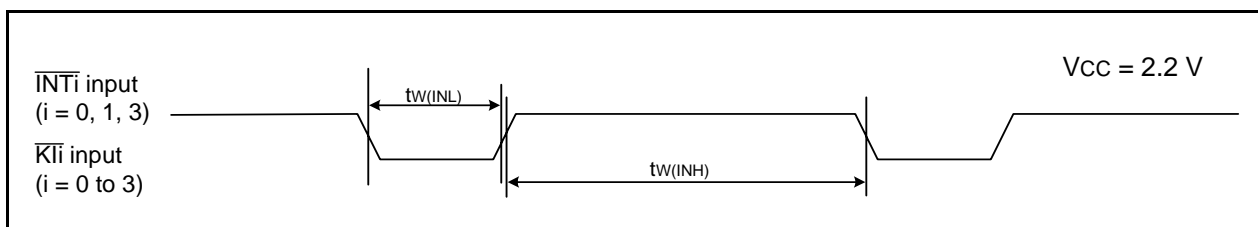
Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	—	ns
$t_{w(CKH)}$	CLKi input "H" width	400	—	ns
$t_{w(CKL)}$	CLKi input "L" width	400	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	150	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

 $i = 0, 2$ **Figure 5.18 Serial Interface Timing Diagram when $V_{cc} = 2.2\text{ V}$** **Table 5.33 External Interrupt \overline{INTi} ($i = 0, 1, 3$) Input, Key Input Interrupt \overline{Kli} ($i = 0$ to 3)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	\overline{INTi} input "H" width, \overline{Kli} input "H" width	1000 ⁽¹⁾	—	ns
$t_{w(INL)}$	\overline{INTi} input "L" width, \overline{Kli} input "L" width	1000 ⁽²⁾	—	ns

Notes:

1. When selecting the digital filter by the \overline{INTi} input filter select bit, use an \overline{INTi} input HIGH width of either (1/digital filter clock frequency $\times 3$) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the \overline{INTi} input filter select bit, use an \overline{INTi} input LOW width of either (1/digital filter clock frequency $\times 3$) or the minimum value of standard, whichever is greater.

**Figure 5.19 Input Timing for External Interrupt \overline{INTi} and Key Input Interrupt \overline{Kli} when $V_{cc} = 2.2\text{ V}$**

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